

A B S T R A C T

A CVD method is to form a silicon nitride film on a target substrate (W). The method includes heating the substrate (W) accommodated in a process container (8), at a process temperature, and supplying a process gas including hexaethylamino-disilane gas and ammonia gas onto the substrate (W) heated at the process temperature, thereby depositing a silicon nitride film on the substrate (W).